

# Si-V (Silicon-Vanadium)

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The Si-V phase diagram in [Massalsi2] was redrawn from [1985Smi].

[2007Zha] noticed that the eutectoid decomposition temperature of  $V_6Si_5$  shown at 1160 °C in [1985Smi], which was quoted from [1985Sto], was actually 1160 K (887 °C). A further investigation by [2007Zha] using x-ray powder diffraction indicated that the decomposition temperature of  $V_6Si_5$  is below 500 °C.

Figure 1 shows the Si-V phase diagram calculated by [2008Zha]. The experimental data points used in the modeling were nearly the same as those used by [1985Smi], but a few additional experiments were carried out to clarify ambiguous areas.

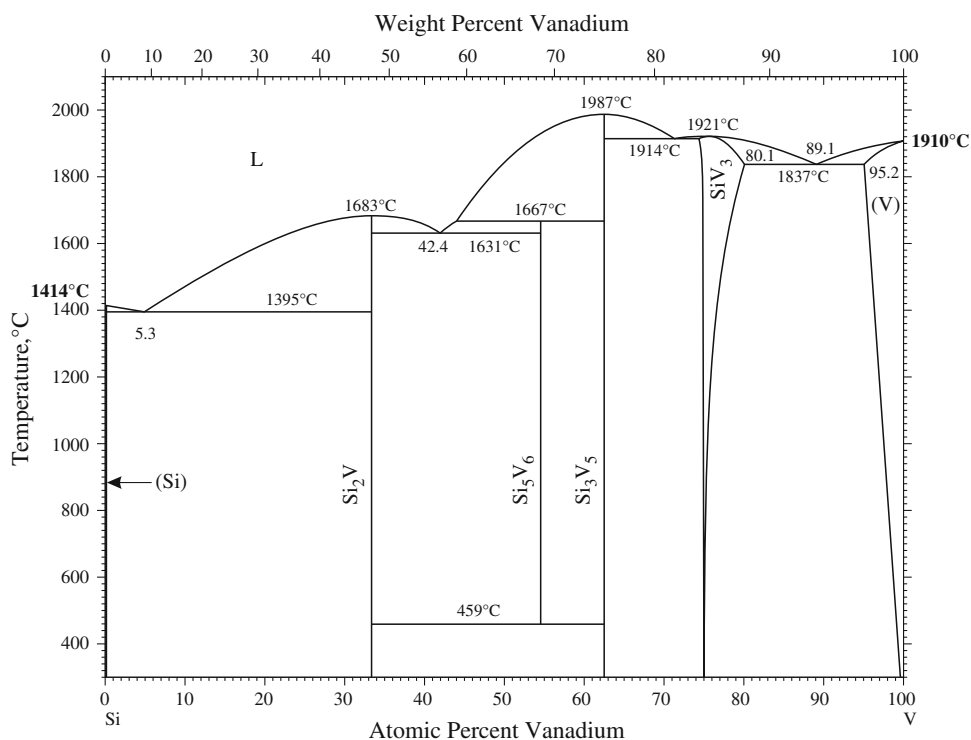
Table 1 shows Si-V crystal structure data given by [1985Smi]. The composition range of phases was modified in accordance with Fig. 1.

## References

- 1985Smi:** J.F. Smith, The Si-V (Silicon-Vanadium) System: Addendum, *Bull. Alloy Phase Diagr.*, 1985, **6**(3), p 266-271  
**1985Sto:** E.K. Storms and C.E. Myers, Thermodynamics and Phase Equilibria in the Vanadium-Silicon System, *High Temp. Sci.*, 1985, **20**, p 87-96

**Table 1** Si-V

Phase	Composition, at.% V	Pearson symbol	Space group	Strukturbericht designation	Prototype
(Si)	0	<i>cF8</i>	<i>Fd<math>\bar{3}m</math></i>	A4	C (diamond)
Si <sub>2</sub> V	33.3	<i>hP9</i>	<i>P6<sub>2</sub>22</i>	C40	CrSi <sub>2</sub>
Si <sub>5</sub> V <sub>6</sub>	55	<i>oI44</i>	<i>Immm</i>	...	Nb <sub>6</sub> Sn <sub>5</sub>
Si <sub>3</sub> V <sub>5</sub>	62.5	<i>tI32</i>	<i>I4/mcm</i>	D8 <sub>m</sub>	W <sub>5</sub> Si <sub>3</sub>
SiV <sub>3</sub>	74.5-80.1	<i>cP8</i>	<i>Pm<math>\bar{3}n</math></i>	A15	Cr <sub>3</sub> Si
(V)	95.2-100	<i>cI2</i>	<i>Im<math>\bar{3}m</math></i>	A2	W



**Fig. 1** Si-V phase diagram

### Section III: Supplemental Literature Review

**2007Zha:** C. Zhang, J. Wang, Y. Du, and W. Zhang, An Investigation on the Thermodynamic Stability of  $V_6Si_5$ , *J. Mater. Sci.*, 2007, **42**, p 7046-7048

**2008Zha:** C. Zhang, Y. Du, W. Xiong, H. Xu, P. Nash, Y. Ouyang, and R. Hu, Thermodynamic Modeling of the V-Si System Supported by Key Experiments, *Calphad*, 2008, **32**, p 320-325